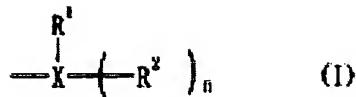


AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings of claims in the application:

LISTING OF CLAIMS:

1. (original) A material for chemical vapor deposition comprising a precursor composed of a metal compound, wherein the material contains 100 or less particles having a size of 0.5 μm or more in 1 ml, in particle measurement by a light scattering type submerged particle detector in a liquid phase.
- 2 (original) The material for chemical vapor deposition according to claim 1, wherein the number of particles having a size of 0.3 μm or more is 100 or less in 1 ml, in particle measurement by a light scattering type submerged particle detector.
3. (currently amended) The material for chemical vapor deposition according to claim 1 [[or 2]], wherein the number of particles having a size of 0.2 μm or more is 1000 or less in 1 ml, in particle measurement by a light scattering type submerged particle detector.
4. (original) The material for chemical vapor deposition according to claim 3, wherein the number of particles having a size of 0.2 μm or more is 100 or less in 1 ml, in particle measurement by a light scattering type submerged particle detector.
5. (currently amended) The material for chemical vapor deposition according to ~~any one of claims 1 to 4~~ claim 1, wherein the precursor is composed of a metal compound having a structure wherein the group represented by general formula (I) shown below bonds to the metal atom:



wherein X represents an oxygen atom or a nitrogen atom; n represents 0 when X is an oxygen atom or n represents 1 when X is a nitrogen atom; R¹ represents an organic group having 1 to 10 carbon atoms; and R² represents a hydrogen atom or an organic group having 1 to 10 carbon atoms.

6. (currently amended) The material for chemical vapor deposition according to ~~any one of claims 1 to 4~~ claim 1, wherein the precursor is composed of a metal compound having a structure wherein the group represented by general formula (II) shown below bonds to the metal atom:



wherein R³ represents an alkyl group having 1 to 8 carbon atoms or a cyclopentadienyl group having 1 to 10 carbon atoms.

7. (currently amended) The material for chemical vapor deposition according to ~~any one of claims 1 to 6~~ claim 1, wherein the metal compound is selected from an aluminum compound, a titanium compound, a zirconium compound, a hafnium compound, a tantalum compound, and a niobium compound.

8. (original) The material for chemical vapor deposition according to claim 7, wherein the metal compound is a hafnium compound.
9. (currently amended) The material for chemical vapor deposition according to ~~any one of claims 1 to 8~~ claim 1, which is delivered or fed in a liquid phase.
10. (currently amended) A method for forming metal-containing thin films by chemical vapor deposition process using the material for chemical vapor deposition according to ~~any one of claims 1 to 9~~ claim 1.
11. (new) The material for chemical vapor deposition according to claim 2, wherein the number of particles having a size of 0.2 μm or more is 1000 or less in 1 ml, in particle measurement by a light scattering type submerged particle detector.